

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (canceled)

7. (currently amended) An integrated circuit structure, comprising:

a gate structure formed on a body of semiconductor material;
an insulating layer of a insulating material formed opposite said gate structure beneath said semiconductor material having a first region beneath said gate structure, the first region extending through the thickness of the insulating layer and free of the insulating material;

a conducting region within said first region, extending through the thickness of the insulating layer beneath said gate structure, said conducting region having sublithographic width.

8. (original) The integrated circuit of Claim 7, wherein said conducting region contacts said semiconductor material.

9. (original) The integrated circuit of Claim 7, wherein said conducting region is formed in a trench with sidewalls.

10. (original) The integrated circuit of Claim 7, wherein said semiconductor material is silicon.

11. (original) The integrated circuit of Claim 7, wherein said conducting region is separated from said semiconductor material by a dielectric material.

12-29. (canceled)